

Description

The AP6679GH-HF uses advanced trench technology

to provide excellent R_{DS(ON)}, low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

General Features

 $V_{DS} = -30V I_{D} = 80 A$

 $R_{DS(ON)}$ < 8.8 m Ω @ V_{GS} =10V

Application

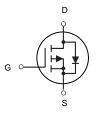
Battery protection

Load switch

Uninterruptible power supply







P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AP6679GH-HF	TO-252-2L (DPAK)	HXY MOSFET	2500

Absolute Maximum Ratings (T_C=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units	
V _D s	Drain-Source Voltage	ource Voltage -30		
Vgs	Gate-Source Voltage	±25	V	
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -10V ¹	-80	А	
I _D @T _C =100°C	Continuous Drain Current, V _{GS} @ -10V ¹	-42	А	
Ідм	Pulsed Drain Current ²	-172	Α	
EAS	Single Pulse Avalanche Energy ³	31	mJ	
las	Avalanche Current	-25		
P _D @T _C =25°C	Total Power Dissipation ⁴	31.2	W	
P _D @T _A =25°C	Total Power Dissipation ⁴	2	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
R ₀ JA	Thermal Resistance Junction-Ambient ¹	43	°C/W	
Rejc	Thermal Resistance Junction-Case ¹	4	°C/W	



Electrical Characteristics T_c = 25°C, unless otherwise noted

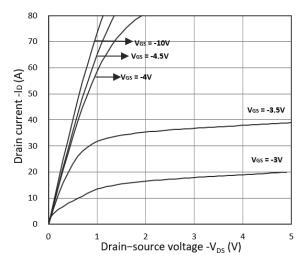
Parameter		Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Drain-Source Breakdown Voltage		V _{(BR)DSS}	V _{GS} = 0V, I _D = -250µA	-30	-	-	V	
Gate-body Leakage current	Gate-body Leakage current		V _{DS} = 0V, V _{GS} = ±20V	-	-	±100	nA	
Zero Gate Voltage Drain Current	T _J =25°C		V _{DS} = -24V, V _{GS} = 0V	-	-	-1	μA	
	T _J =55°C	I _{DSS}		-	-	-5		
Gate-Threshold Voltage		V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-1.0	-1.6	-2.5	V	
Drain-Source On-Resistance ²		_	V _{GS} = -10V, I _D = -12A	-	5.5	8.8	0	
		R _{DS(on)}	V _{GS} = -4.5V, I _D = -8A	-	9	14	mΩ	
Forward Transconductance		G fs	V _{DS} = -5V, I _D = -20A	-	28	-	S	
Input Capacitance		Ciss	V _{DS} = -15V, V _{GS} =0V, f =1MHz	-	4320	-	pF	
Output Capacitance		Coss		-	529	-		
Reverse Transfer Capacitance		C _{rss}		-	487	-		
Gate Resistance		Rg	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$	-	4.0	-	Ω	
Total Gate Charge	Total Gate Charge		V _{GS} = -10V, V _{DS} = -15V, I _D = -15A	-	45	-	nC	
Gate-Source Charge		Q_{gs}		-	8.5	-		
Gate-Drain Charge		\mathbf{Q}_{gd}		-	12.8	-		
Turn-On Delay Time		t _{d(on)}		-	18.9	-	. nS	
Rise Time		t r	$V_{GS} = -10V, V_{DD} = -15V,$	-	15.7	-		
Turn-Off Delay Time		t _{d(off)}	$R_G = 2.5\Omega$, $I_D = -15A$	-	64.8	-		
Fall Time		t f		-	36.5	-		
Diode Forward Voltage ²		V _{SD}	I _S = -1A, V _{GS} = 0V	-	-	-1	V	
Continuous Source Current ^{1,5}		Is	V _G =V _D =0V , Force Current	-	-	-80	Α	

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300 us$, duty cycle $\leq 2\%$
- 3. The EAS data shows Max. rating . The test condition is V_{DD} = -25V, V_{GS} = -10V, L= 0.1mH, I_{AS} = -25A
- 4.The power dissipation is limited by 150 $^{\circ}\text{C}\,$ junction temperature
- 5. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.



Typical Characteristics



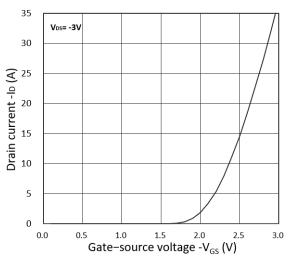


Figure 1. Output Characteristics

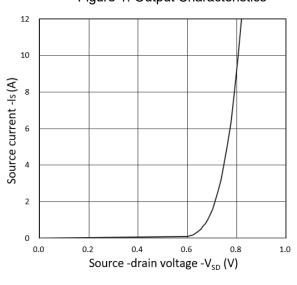


Figure 2. Transfer Characteristics

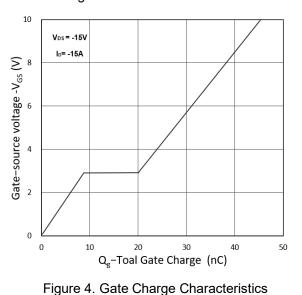
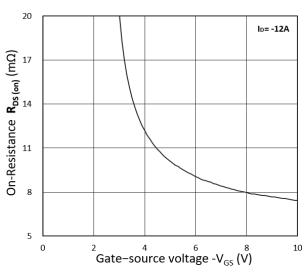


Figure 3. Forward Characteristics of Reverse



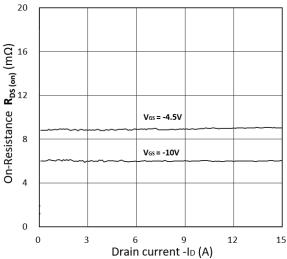


Figure 5. RDS(on) vs. VGS

Figure 6. R_{DS(on)} vs. I_D



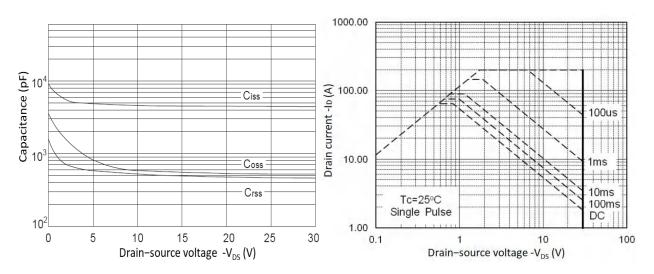


Figure 7. Capacitance Characteristics

Figure 8. Safe Operating Area

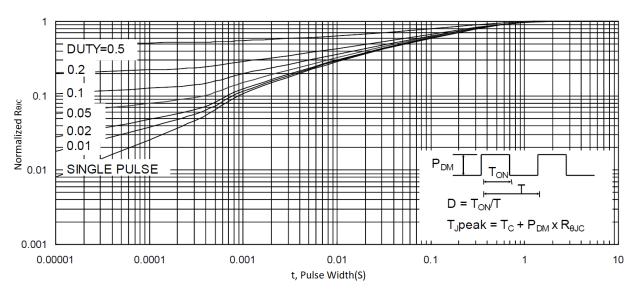


Figure 9. Normalized Maximum Transient Thermal Impedance

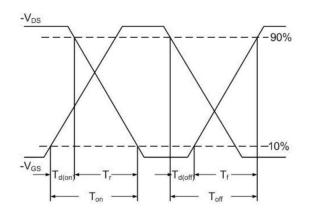


Figure 10. Switching Time Waveform

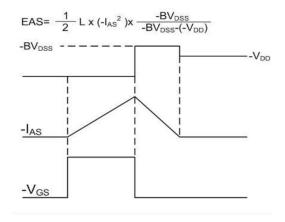


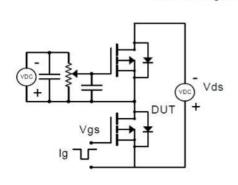
Figure 11. Unclamped Inductive Switching

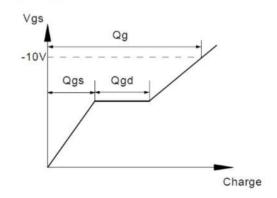
Waveform



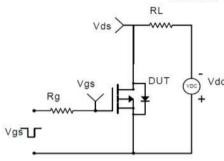
Test Circuit

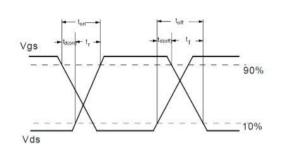
Gate Charge Test Circuit & Waveform



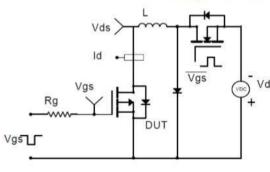


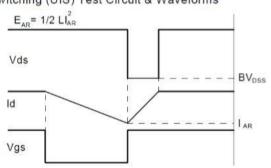
Resistive Switching Test Circuit & Waveforms



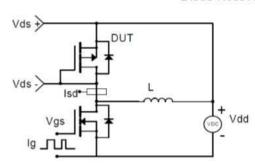


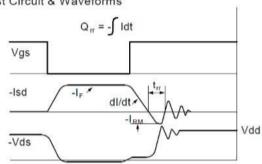
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms





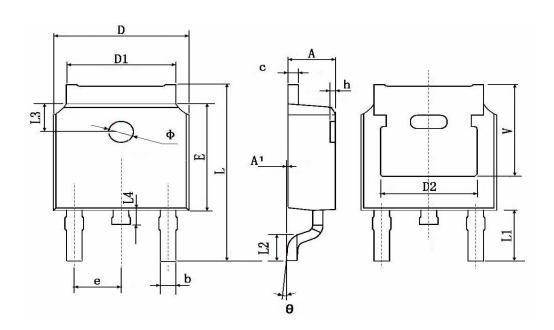
Diode Recovery Test Circuit & Waveforms







TO-252-2L(DPAK) Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	2.200	2.400	0.087	0.094	
A1	0.000	0.127	0.000	0.005	
b	0.660	0.860	0.026	0.034	
С	0.460	0.580	0.018	0.023	
D	6.500	6.700	0.256	0.264	
D1	5.100	5.460	0.201	0.215	
D2	4.830 TYP.		0.190 TYP.		
Е	6.000	6.200	0.236	0.244	
е	2.186	2.386	0.086	0.094	
L	9.800	10.400	0.386	0.409	
L1	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067	
L3	1.600 TYP.		0.063 TYP.		
L4	0.600	1.000	0.024	0.039	
Ф	1.100	1.300	0.043	0.051	
θ	0°	8°	0°	8°	
h	0.000	0.300	0.000	0.012	
V	5.350 TYP.		0.211 TYP.		

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